

Super high speed Evaporator System

(초고속 진공 증착기)

Specification

Chamber



Main Chamber: Rectangular Type

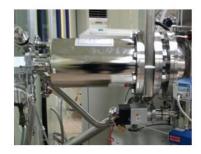
Loading Chamber: Circular Type (Optional)

Material: SUS 304

Chamber internal shield cover

(Easy exchange type)

Vacuum pump



Turbo pump or Cryo Pump (Optional)

Rotary pump (Optional : Dry pump)

High Vacuum Gate Valve

Substrate



Sample Size : Piece ~ 6" Wafer (Etc Optional)

Single sample Rotation Type (One process)

Multi sample Rotation Type (One process)

Rotation & Revolution Substrate (Optional)

Substrate Shutter

Rotation speed: 0 ~ 30 R.P.M

Revolution speed: 0 ~ 30 R.P.M

Daedong Hightechnologies



Super high speed Evaporator System

(초고속 진공 증착기)

Specification

Thickness Monitor







Thickness Monitor or Controller (Optional)

Rate Monitoring or Rate Control type

Rate Resolution: Below than 0.1Å/Sec

Single or Dual sensor mount type (Multi sensor is optional)

Co-deposition available (Optional)

Thickness sensor Shutter (Optional)

Supply Brand (Inficon or Sycon)

Source & Power Supply





Source : Induction Coil & Crucible (Optional)

Crucible Size: 15cc ~ 100cc (Optional)

Source Housing Water Cooling

Induction Coil Water Cooling

Induction Power Frequency: 10~30KHz

Power Capacity: 10kW ~ Optional

Inside water cooling

Source Shutter



Super high speed Evaporator System

(초고속 진공 증착기)

Specification	
Required Services	Main Power : 220V or 380V, 3 Phase, 50A
	PCW (Water): 2~3kgf/Cm2
	Compressed Air : 5.5~6 Kgf/Cm2
	N2 Gas (Chamber Vent) : 1~2 Kgf/Cm2
	Exhaust : Ø40 Flexible Hose

Remark

Chamber Ultimate Pressure (One Chamber type)

; Below than 2×10^{-7} Torr

Pumping speed (One Chamber type) : Below than 5×10^{-6} Torr

; Below than 3×10^{-6} Torr (Within 30 Minute after Sample loading)

Film deposition Uniformity : Below than ±5%

Deposition Rate control range: 1Å/Sec ~ 1000Å/Sec

(Thin film ~ thick film control available)

Deposition Material: Cu, Al, Ag, etc Metal Process

Application

Fast thick film deposition process

Deposition Rate: More than 1000Å/Sec

- ② Instead of wet plating (Cu, Al, Ag, Cr, Ni, etc metal film)
- ③ TSV (Through silicon via) Process